

CMKD6001

SURFACE MOUNT
ULTRAmimi™
TRIPLE ISOLATED
LOW LEAKAGE SILICON
SWITCHING DIODES

ULTRAmimi™

SOT-363 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKD6001 type contains three (3) Isolated Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a ULTRAmimi™ surface mount package, designed for switching applications requiring extremely low leakage.

MARKING CODE: K01

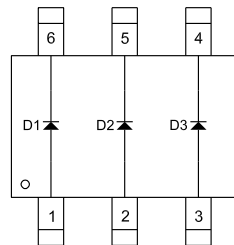
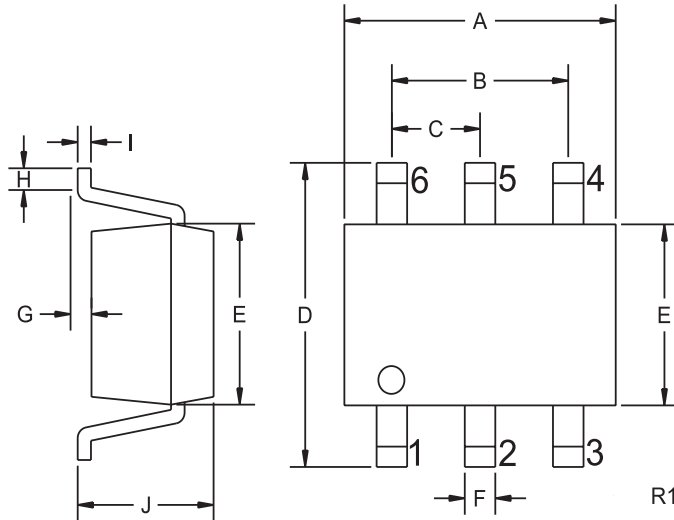
MAXIMUM RATINGS: (T _A =25°C)			
Continuous Reverse Voltage	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V _R	75	V
Continuous Forward Current	V _{RRM}	100	V
Peak Repetitive Forward Current	I _F	250	mA
Forward Surge Current, tp=1 µsec.	I _{FRM}	500	mA
Forward Surge Current, tp=1 sec.	I _{FSM}	4000	mA
Power Dissipation	I _{FSM}	1000	mA
Operating and Storage	P _D	250	mW
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	Θ _{JA}	500	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _R	V _R =75V		500	pA
BV _R	I _R =100µA	100		V
V _F	I _F =1.0mA		0.85	V
V _F	I _F =10mA		0.95	V
V _F	I _F =100mA		1.1	V
C _T	V _R =0, f=1 MHz		2.0	pF
t _{rr}	I _R =I _F =10mA, R _L =100Ω Rec. to 1.0mA		3.0	µs

**SURFACE MOUNT
ULTRAmini™
TRIPLE ISOLATED
LOW LEAKAGE SILICON
SWITCHING DIODES**

SOT-363 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) ANODE D1
- 2) ANODE D2
- 3) ANODE D3
- 4) CATHODE D3
- 5) CATHODE D2
- 6) CATHODE D1

MARKING CODE: K01

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.073	0.085	1.85	2.15
B	0.051		1.30	
C	0.026		0.65	
D	0.075	0.091	1.90	2.30
E	0.043	0.055	1.10	1.40
F	0.006	0.012	0.15	0.30
G	0.000	0.004	0.00	0.10
H	0.010	-	0.25	-
I	0.004	0.010	0.10	0.25
J	0.031	0.039	0.80	1.00

SOT-363 (REV: R1)

R2 (7-August 2003)